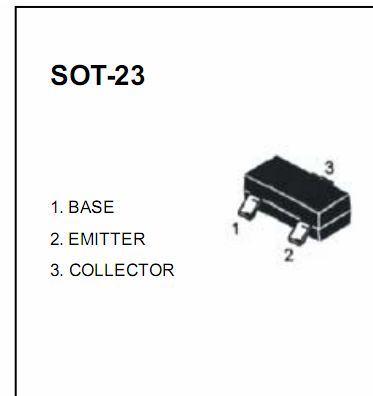


2SA812

SOT-23 Plastic-Encapsulate Transistors

TRANSISTOR (PNP)

MARKING:M6



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol (符号)	Parameter (参数名称)	Value (额定值)	Units (单位)
VCBO	Collector-Base Voltage (集电极-基极电压)	-50	V
VCEO	Collector-Emitter Voltage (集电极-发射极电压)	-45	V
VEBO	Emitter-Base Voltage (发射极-基极电压)	-5	V
IC	Collector Current -Continuous (集电极电流)	-0.1	A
PC	Collector Power Dissipation (耗散功率)	0.2	W
Tj	Junction Temperature (结温)	150	°C
Tstg	Storage Temperature (储存温度)	-55-150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter (参数名称)	Symbol (符号)	Test conditions (测试条件)	MIN (最小值)	TYP (典型值)	MAX (最大值)	UNIT (单位)
Collector-base breakdown voltage 集电极-基极击穿电压	V(BR)CBO	IC= -100μA, IE=0	-50			V
Collector-emitter breakdown voltage 集电极-发射极击穿电压	V(BR)CEO	IC= -1mA, IB=0	-45			V
Emitter-base breakdown voltage 发射极-基极击穿电压	V(BR)EBO	IE=-100μA, IC=0	-5			V
Collector cut-off current 集电极-基极截止电流	ICBO	VCB=-50 V, IE=0			-1	μ A
Collector cut-off current 集电极-发射极截止电流	ICEO	VCE=-35V, IB=0			-10	μ A
Emitter cut-off current 发射极-基极截止电流	IEBO	VEB=-5V, IC=0			-1	μ A
DC current gain 直流电流增益	hFE	VCE=-5V, IC= -1mA	80		600	
Collector-emitter saturation voltage 集电极-发射极饱和压降	VCE(sat)	IC=-100mA, IB= -5mA			-0.3	V
Base-emitter saturation voltage 发射极-基极饱和压降	VBE(sat)	IC=-100mA, IB= -5mA			-1	V

CLASSIFICATION OF hFE

Range	80-200	200-400	400-600

Typical Characteristics

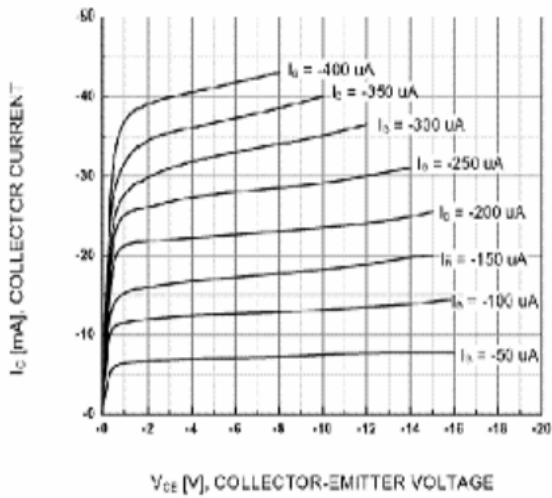


Figure 1. Static Characteristic

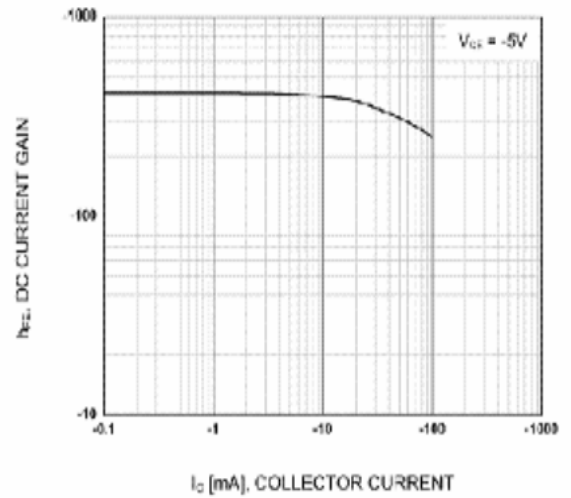


Figure 2. DC current Gain

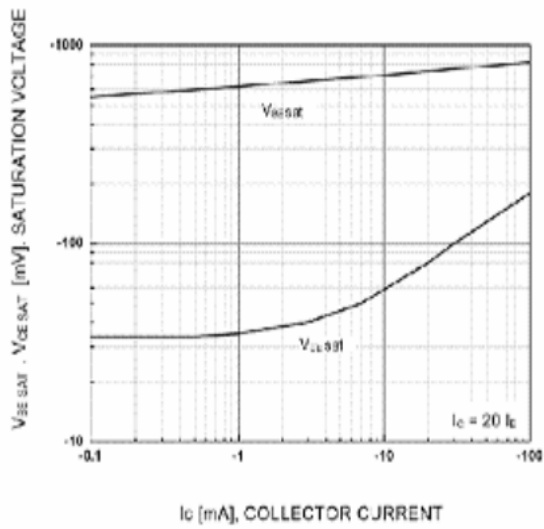


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

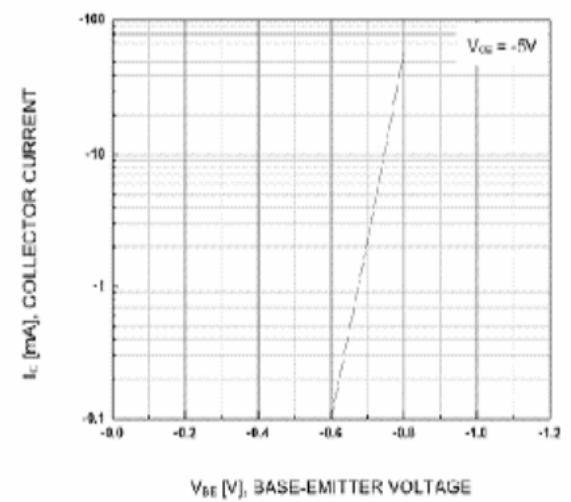


Figure 4. Base-Emitter On Voltage